
2SC4643

Silicon NPN Epitaxial

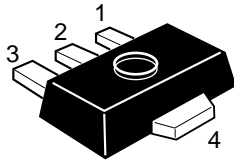
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Application

UHF / VHF wide band amplifier

Outline

UPAK



- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector (Flange)

Absolute Maximum Ratings (Ta = 25°C)

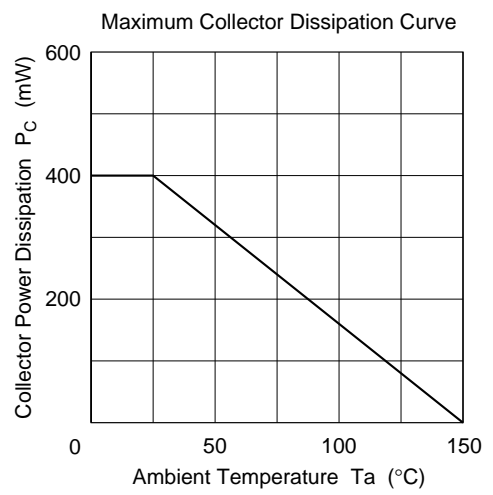
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	9	V
Emitter to base voltage	V_{EBO}	1.5	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	400	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

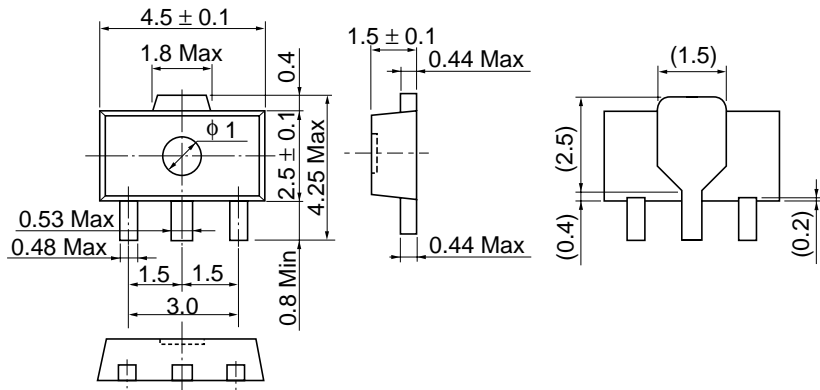
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	—	—	V	$I_C = 10\text{ }\mu\text{A}$, $I_E = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{CB} = 12\text{ V}$, $I_E = 0$
	I_{CEO}	—	—	1	mA	$V_{CE} = 9\text{ V}$, $R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 1.5\text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}	40	120	250	—	$V_{CE} = 5\text{ V}$, $I_C = 20\text{ mA}$
Collector output capacitance	C_{ob}	—	1.0	1.7	pF	$V_{CB} = 5\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$
Gain bandwidth product	f_T	5.5	8.0	—	GHz	$V_{CE} = 5\text{ V}$, $I_C = 20\text{ mA}$
Power gain	PG	7.5	10.5	—	dB	$V_{CE} = 5\text{ V}$, $I_C = 20\text{ mA}$, $f = 900\text{ MHz}$
Noise figure	NF	—	1.2	2.5	dB	$V_{CE} = 5\text{ V}$, $I_C = 5\text{ mA}$, $f = 900\text{ MHz}$

Note: Marking is “DR”.

See characteristic curve of 2SC4592





Hitachi Code	UPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.050 g

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